

BTA/BTB24, BTA25, BTA26 and T25 Series

SNUBBERLESS™ & STANDARD

25A TRIACs

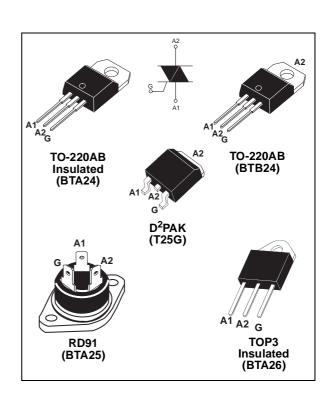
MAIN FEATURES:

Symbol	Value	Unit
I _{T(RMS)}	25	Α
V _{DRM} /V _{RRM}	600 and 800	V
I _{GT (Q₁)}	35 to 50	mA

DESCRIPTION

Available either in through-hole of surface and T25 mount packages, the BTA/BTB24-25-26 triac series is suitable for general purpose AC power switching. They can be used as an ON/OFF function in applications such as static relays, heating regulation, water heaters, induction motor starting circuits...or for phase control operation in high power motor speed controllers, soft start circuits...The snubberless versions (BTA/BTB...W and T25 series) are specially recommended for use on inductive loads, thanks to their high commutation performances.

By using an internal ceramic pad, the BTA series provides voltage insulated tab (rated at 2500V RMS) complying with UL standards (File ref.: E81734).



ABSOLUTE MAXIMUM RATINGS

Symbol	Parame		Value	Unit	
I _{T(RMS)}	RMS on-state current (full sine wave)	D²PAK TO-220AB	Tc = 100°C		Α
		RD91 TOP3 Ins.	Tc = 90°C	25	
		TO-220AB Ins.	Tc = 75°C		
I _{TSM}	3 1 2 2 3 1 2 2 2 2 2 2 2 2 2 2 2 2 2 2		t = 16.7 ms	260	Α
	current (full cycle, Tj initial = 25°C)	F = 50 Hz	t = 20 ms	250	
l ² t	I ² t Value for fusing	tp = 10 i	ms	340	A ² s
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, tr $\leq 100 \text{ ns}$	F = 120 Hz	Tj = 125°C	50	A/µs
V _{DSM} /V _{RSM}	Non repetitive surge peak off-state voltage	tp = 10 ms	Tj = 25°C	V _{DRM} /V _{RRM} + 100	V
I _{GM}	Peak gate current	tp = 20 μs	Tj = 125°C	4	Α
P _{G(AV)}	Average gate power dissipation		Tj = 125°C	1	W
T _{stg} T _j	Storage junction temperature range Operating junction temperature range		•	- 40 to + 150 - 40 to + 125	°C

September 2002 - Ed: 6A 1/9

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ELECTRICAL CHARACTERISTICS (Tj = 25°C, unless otherwise specified)

■ SNUBBERLESS™ (3 Quadrants) T25-G, BTA/BTB24...W, BTA25...W, BTA26...W

Symbol	Test Conditions	Quadrant		T25 BTA/BTB		/ВТВ	Unit
				T2535	CW	BW	
I _{GT} (1)	$V_{\rm D} = 12 {\rm V}$ $R_{\rm I} = 33 {\rm \Omega}$	1 - 11 - 111	MAX.	35	35	50	mA
V _{GT}	1 VD = 12 V	1 - 11 - 111	MAX.		1.3		V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $Tj = 125^{\circ}\text{C}$	1 - 11 - 111	MIN.	0.2			V
I _H (2)	I _T = 500 mA		MAX.	50	50	75	mA
IL	$I_G = 1.2 I_{GT}$	I - III	MAX.	70	70	80	mA
		II		80	80	100	
dV/dt (2)	$V_D = 67 \% V_{DRM}$ gate open $Tj = 125$ °C		MIN.	500	500	1000	V/µs
(dl/dt)c (2)	Without snubber Tj = 125	°C	MIN.	13	13	22	A/ms

■ STANDARD (4 Quadrants): BTB24...B, BTA25...B, BTA26...B

Symbol	Test Conditions	Quadrant		Value	Unit
I _{GT} (1)	$V_D = 12 \text{ V}$ $R_L = 33 \Omega$	I - II - III IV	MAX.	50 100	mA
V_{GT}		ALL	MAX.	1.3	V
$V_{\sf GD}$	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $Tj = 125 ^{\circ}\text{C}$	ALL	MIN.	0.2	V
I _H (2)	$I_T = 500 \text{ mA}$		MAX.	80	mA
ΙL	I _G = 1.2 I _{GT}	I - III - IV	MAX.	70	mA
		П		160	
dV/dt (2)	$V_D = 67 \% V_{DRM}$ gate open Tj = 125°C		MIN.	500	V/µs
(dV/dt)c (2)	$(dI/dt)c = 13.3 \text{ A/ms}$ $Tj = 125^{\circ}C$		MIN.	10	V/µs

STATIC CHARACTERISTICS

Symbol	Test Cond	Value	Unit		
V _{TM} (2)	I _{TM} = 35 A tp = 380 μs	Tj = 25°C	MAX.	1.55	V
V _{to} (2)	Threshold voltage	Threshold voltage Tj = 125°C MAX.		0.85	V
R _d (2)	Dynamic resistance Tj = 125°C		MAX.	16	mΩ
I _{DRM}	$V_{DRM} = V_{RRM}$	Tj = 25°C	MAX.	5	μA
I _{RRM}		Tj = 125°C	IVIAA.	3	mA

Note 1: minimum IGT is guaranted at 5% of IGT max.

Note 2: for both polarities of A2 referenced to A1

THERMAL RESISTANCES

Symbol	Para	ameter		Value	Unit
R _{th(j-c)}	Junction to case (AC)		D ² PAK TO-220AB	0.8	°C/W
			RD91 (Insulated) TOP3 Insulated	1.1	
			TO-220AB Insulated	1.7	
R _{th(j-a)}	Junction to ambient	S = 1 cm ²	D ² PAK	45	°C/W
			TOP3 Insulated	50	
			TO-220AB	60	
			TO-220AB Insulated	00	

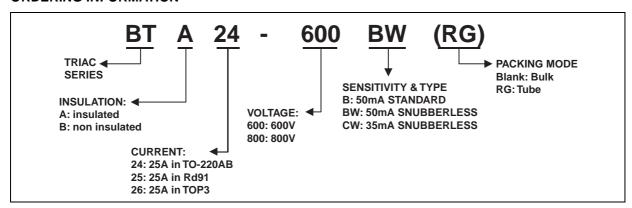
S: Copper surface under tab

PRODUCT SELECTOR

Part Number	Voltag	e (xxx)	Compitivity	Time	Bashana
	600 V	800 V	Sensitivity	Туре	Package
BTB24-xxxB	Х	Х	50 mA	Standard	TO-220AB
BTA/BTB24-xxxBW	Х	Х	50 mA	Snubberless	TO-220AB
BTA/BTB24-xxxCW	Х	Х	35 mA	Snubberless	TO-220AB
BTA25-xxxB	Х	Х	50 mA	Standard	RD-91
BTA25-xxxBW	Х	Х	50 mA	Snubberless	RD-91
BTA25-xxxCW	Х	Х	35 mA	Snubberless	RD-91
BTA26-xxxB	Х	Х	50 mA	Standard	TOP3 Ins.
BTA26-xxxBW	Х	Х	50 mA	Snubberless	TOP3 Ins.
BTA26-xxxCW	Х	Х	35 mA	Snubberless	TOP3 Ins.
T2535-xxxG	Х	Х	35 mA	Snubberless	D ² PAK

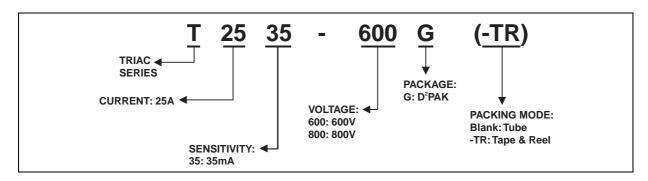
BTB: Non insulated TO-220AB package

ORDERING INFORMATION



57

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OTHER INFORMATION

Part Number	Marking	Weight	Base quantity	Packing mode
BTA/BTB24-xxxyz	BTA/BTB24xxxyz	2.3 g	250	Bulk
BTA/BTB24-xxxyzRG	BTA/BTB24-xxxyz	2.3 g	50	Tube
BTA25-xxxyz	BTA25xxxyz	20 g	25	Bulk
BTA26-xxxyz	BTA26xxxyz	4.5 g	120	Bulk
T2535-xxxG	T2535xxxG	1.5 g	50	Tube
T2535-xxxG-TR	T2535xxxG	1.5 g	1000	Tape & reel

Note: xxx = voltage, y = sensitivity, z = type

Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle).

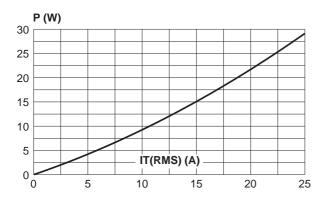


Fig. 2-2: D²PAK RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: $35 \mu m$), full cycle.

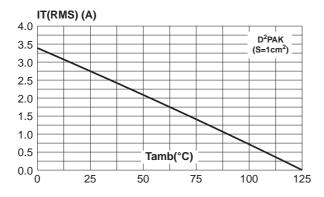


Fig. 4: On-state characteristics (maximum values).

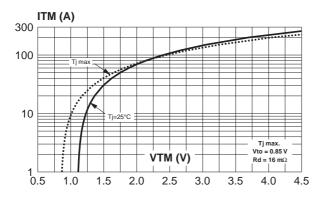


Fig. 2-1: RMS on-state current versus case temperature (full cycle).

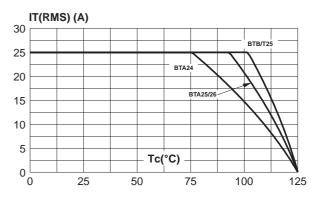


Fig. 3: Relative variation of thermal impedance versus pulse duration.

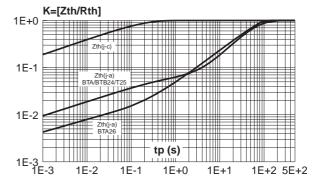
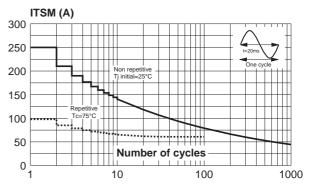


Fig. 5: Surge peak on-state current versus number of cycles.



577

Fig. 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10ms, and corresponding value of I²t.

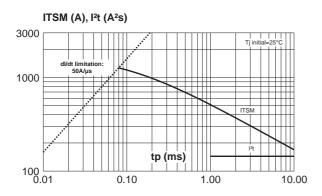


Fig. 8: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values).

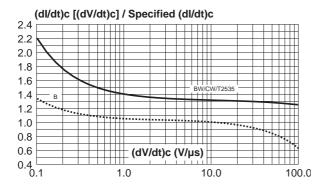


Fig. 10: D²PAK Thermal resistance junction to ambient versus copper surface under tab (printed circuit board FR4, copper thickness: $35 \,\mu m$).

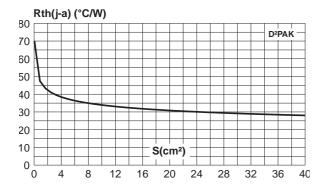


Fig. 7: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).

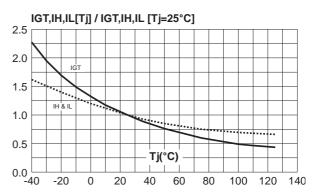
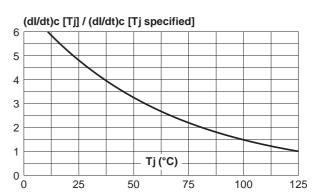
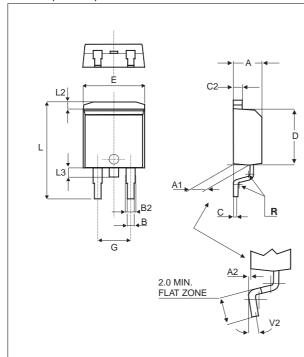


Fig. 9: Relative variation of critical rate of decrease of main current versus junction temperature.



PACKAGE MECHANICAL DATA

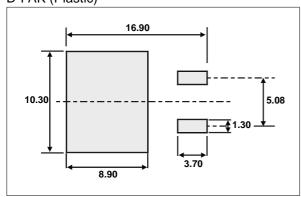
D²PAK (Plastic)



	DIMENSIONS							
REF.	М	illimete	rs	Inches				
	Min.	Тур.	Max.	Min.	Тур.	Max.		
Α	4.30		4.60	0.169		0.181		
A1	2.49		2.69	0.098		0.106		
A2	0.03		0.23	0.001		0.009		
В	0.70		0.93	0.027		0.037		
B2	1.25	1.40		0.048	0.055			
С	0.45		0.60	0.017		0.024		
C2	1.21		1.36	0.047		0.054		
D	8.95		9.35	0.352		0.368		
Е	10.00		10.28	0.393		0.405		
G	4.88		5.28	0.192		0.208		
L	15.00		15.85	0.590		0.624		
L2	1.27		1.40	0.050		0.055		
L3	1.40		1.75	0.055		0.069		
R		0.40			0.016			
V2	0°		8°	0°		8°		

FOOTPRINT DIMENSIONS (in millimeters)

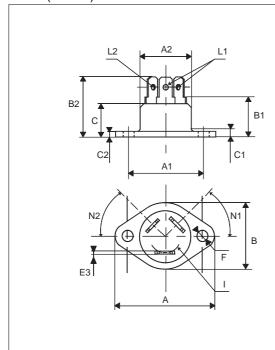
D²PAK (Plastic)



577

PACKAGE MECHANICAL DATA

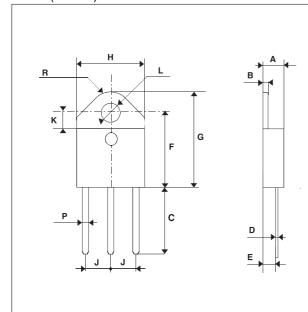
RD91 (Plastic)



	DIMENSIONS						
REF.	Millin	neters	Inc	hes			
	Min.	Max.	Min.	Max.			
Α		40.00		1.575			
A1	29.90	30.30	1.177	1.193			
A2		22.00		0.867			
В		27.00		1.063			
B1	13.50	16.50	0.531	0.650			
B2		24.00		0.945			
С		14.00		0.551			
C1		3.50		0.138			
C2	1.95	3.00	0.077	0.118			
E3	0.70	0.90	0.027	0.035			
F	4.00	4.50	0.157	0.177			
ı	11.20	13.60	0.441	0.535			
L1	3.10	3.50	0.122	0.138			
L2	1.70	1.90	0.067	0.075			
N1	33°	43°	33°	43°			
N2	28°	38°	28°	38°			

PACKAGE MECHANICAL DATA

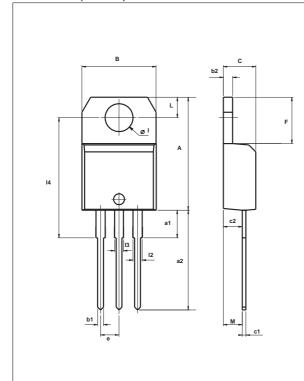
TOP3 (Plastic)



REF.	Millimeters		rs	s Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.4		4.6	0.173		0.181
В	1.45		1.55	0.057		0.061
С	14.35		15.60	0.565		0.614
D	0.5		0.7	0.020		0.028
Е	2.7		2.9	0.106		0.114
F	15.8		16.5	0.622		0.650
G	20.4		21.1	0.815		0.831
Н	15.1		15.5	0.594		0.610
J	5.4		5.65	0.213		0.222
K	3.4		3.65	0.134		0.144
L	4.08		4.17	0.161		0.164
Р	1.20		1.40	0.047		0.055
R		4.60			0.181	

PACKAGE MECHANICAL DATA

TO-220AB (Plastic)



			DIMEN	SIONS		
REF.	Millimeters		rs			
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
В	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
С	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
е	2.40		2.70	0.094		0.106
F	6.20		6.60	0.244		0.259
I	3.75		3.85	0.147		0.151
14	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
12	1.14		1.70	0.044		0.066
13	1.14		1.70	0.044		0.066
М		2.60			0.102	

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